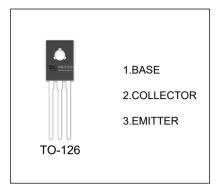


3DD13003 TRANSISTOR (NPN)

FEATURES

Power switching applications



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
3DD13003	TO-126	Bulk	200pcs/Bag
3DD13003-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
Ic	Collector Current -Continuous	1.5	Α
Pc	Collector Power Dissipation	1.5	W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~150	℃



T_a =25 $^{\circ}$ C unless otherwise specified

Parameter	symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =5mA, I _E =0	700			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =2mA, I _C =0	9			V
Collector cut-off current	I _{CBO}	V _{CB} =700V,I _E =0			1	mA
Collector cut-off current	I _{CEO}	V _{CE} =400V,I _B =0			0.5	mA
Emitter cut-off current	I _{EBO}	V _{EB} =9V, I _C =0			1	mA
DC current gain	h _{FE1}	V _{CE} =5V, I _C = 0.5 A	20		40	
	h _{FE2}	V _{CE} =5V, I _C = 1.5A	5			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1A,I _B =0.25A			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =1A,I _B =0.25A			1.2	V
Transition frequency	f _T	V _{CE} =10V,Ic=100mA, f=1MHz	5			MHz
Fall time	t _f	I _C =1A, I _{B1} =-I _{B2} =0.2A, V _{CC} =100V			0.5	μs
Storage time	t _s	I _C =250mA (UI9600)	2		4	μs

CLASSIFICATION OF h_{FE(1)}

Range	20-30	30-40

CLASSIFICATION OF t_S

Rank	А	В
Range	2.0-3.0 (μs)	3.0-4.0(μ s)



